Workshop on quantum dot based devices for long wavelength sources and single photon sources

CNRS/LPN Marcoussis 10th-11th February 2005

Thursday

11:00 – 11:20	Presentation of LPN (Jean-Yves Marzin, Director)
11:20 – 11:30	Device activities within SANDiE: JPR-A, JPR-C, Reporting-form (A Ramdane, A Shields)
11:30 – 12:00	Quantum dots for tuneable lasers (David Childs, Bookham)
12:00 – 12:30	Telecom wavelength single photon sources (Martin Ward, Toshiba Europe)
	Lunch
14:00 – 14:30	Memory of a GaAs/(AlGa)As field effect transistor incorporating quantum dots (Richard Hill, University of Nottingham)
14:30 – 15:00	Long-wavelength In(Ga)As/GaAs quantum dot based lasers grown by MOVPE (Guillaume Saint Girons, LPN)
15:00 – 15:30	1.3 µm InGaAs/GaAs Quantum dot Devices: VCSEL, Edge Emitter and Amplifier (Friedhelm Hopfer, University of Berlin)
15:30 – 16:30	Coffee break Discussions
Friday	
9:00 – 9:30	Development of 1.3 μm quantum dot lasers and 1.0μm and 1.3 μm single photon sources (David Mowbray, University of Sheffield)
9:30 – 10:00	InAs/InP (311)B quantum dot active medium for 1.55 µm telecommunication devices (Nicolas Bertru, INSA-LENS Rennes
10:00 - 10:30	MBE grown InAs/GaAs QD lasers and amplifiers (Anthony Martinez, LPN)